## **ABSTRACT**

A semiconductor circuit with a depletion-mode transistor is formed with a method that eliminates the need for a separate mask and implant step to set the threshold voltage of the depletion-mode transistor. As a result, the method of the present invention reduces the cost and complexity associated with the fabrication of a semiconductor circuit that includes a depletion-mode transistor.

10

5

10488071v1 072219-0276257 [PO4927]